

**Table 4.1.** Experimental binding energies of the 1s state of shallow donors in some zinc-blende-type semiconductors (from [Ref. 4.4, p. 224]) compared with the predictions of (4.24)

Semiconductor	Binding energy from (4.24) [meV]	Experimental binding energy of common donors [meV]
GaAs	5.72	Si <sub>Ga</sub> (5.84); Ge <sub>Ga</sub> (5.88) S <sub>As</sub> (5.87); Se <sub>As</sub> (5.79)
InP	7.14	7.14
InSb	0.6	Te <sub>Sb</sub> (0.6)
CdTe	11.6	In <sub>Cd</sub> (14); Al <sub>Cd</sub> (14)
ZnSe	25.7	Al <sub>Zn</sub> (26.3); Ga <sub>Zn</sub> (27.9) F <sub>Se</sub> (29.3); Cl <sub>Se</sub> (26.9)